

Silicon PNP Power Transistors

2SA756

DESCRIPTION

- With TO-3 package
- Complement to type 2SC1030

APPLICATIONS

- For audio amplifier power output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

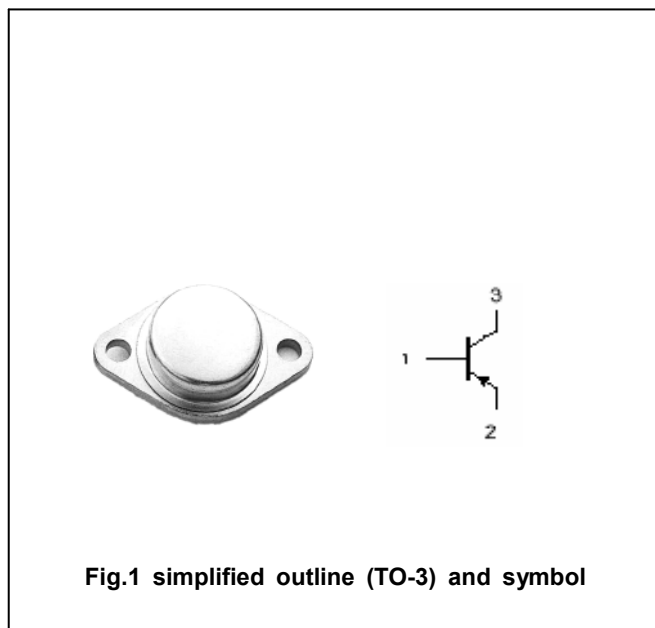


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector-emitter voltage	Open base	-80	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-6	A
P _C	Collector power dissipation	T _C =25□	50	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA ; R _{BE} =∞	-80			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-5mA , I _E =0	-100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-5mA , I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-5A; I _B =-1A			-1.8	V
V _{BE}	Base-emitter on voltage	I _C =-1A ; V _{CE} =-5V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-30V; I _E =0			-1	mA
h _{FE-1}	DC current gain	I _C =-1A ; V _{CE} =-5V	35		200	
h _{FE-2}	DC current gain	I _C =-5A ; V _{CE} =-5V	20			
f _T	Transition frequency	I _C =-1A ; V _{CE} =-5V		20		MHz

◆ h_{FE-1} Classifications

A	B	C
35-70	60-120	100-200

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)